

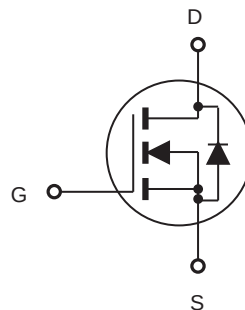
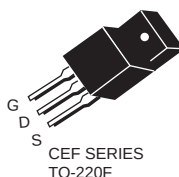
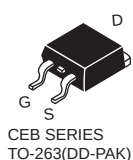
CEP02N7/CEB02N7 CEI02N7/CEF02N7

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP02N7	700V	6.6Ω	1.9A	10V
CEB02N7	700V	6.6Ω	1.9A	10V
CEI02N7	700V	6.6Ω	1.9A	10V
CEF02N7	700V	6.6Ω	1.9A ^e	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-262 package & TO-220F full-pak for through hole.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263/262	TO-220F	
Drain-Source Voltage	V _{DS}	700		V
Gate-Source Voltage	V _{GS}	±30		V
Drain Current-Continuous	I _D	1.9	1.9 ^e	A
Drain Current-Pulsed ^a	I _{DM} ^f	6	6 ^e	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P _D	60	32	W
		0.48	0.26	W/°C
Single Pulsed Avalanche Energy ^d	E _{AS}	125	125	mJ
Repetitive Avalanche Current ^a	I _{AR}	2	2	A
Repetitive Avalanche Energy ^a	E _{AR}	5.4	5.4	mJ
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	2.1	3.9	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W

查询"CEB02N7"供应商

CEP02N7/CEB02N7 CEI02N7/CEF02N7

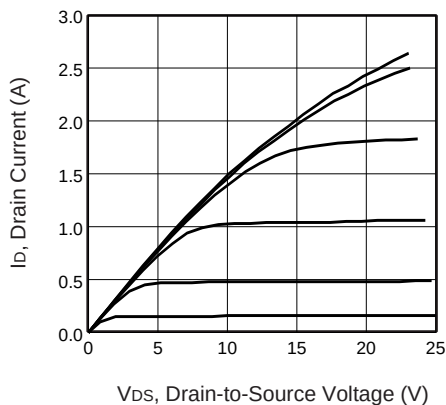


Figure 1. Output Characteristics

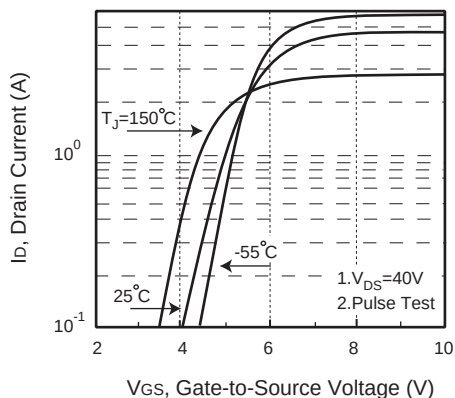


Figure 2. Transfer Characteristics

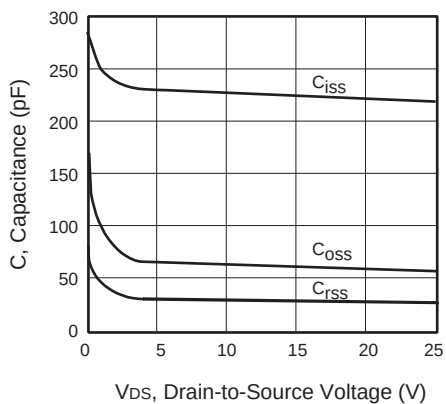


Figure 3. Capacitance

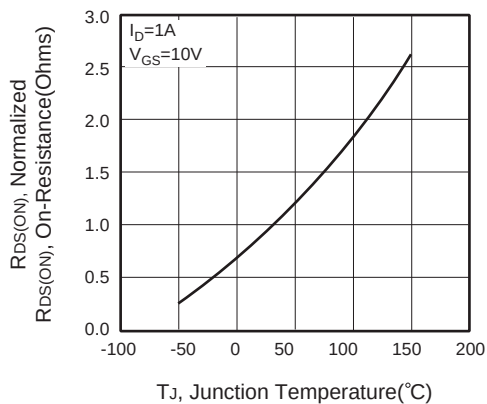


Figure 4. On-Resistance Variation with Temperature

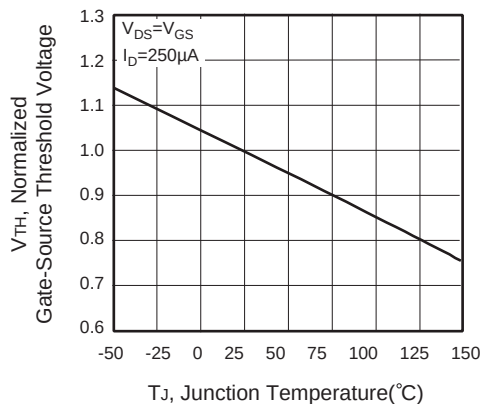


Figure 5. Gate Threshold Variation with Temperature

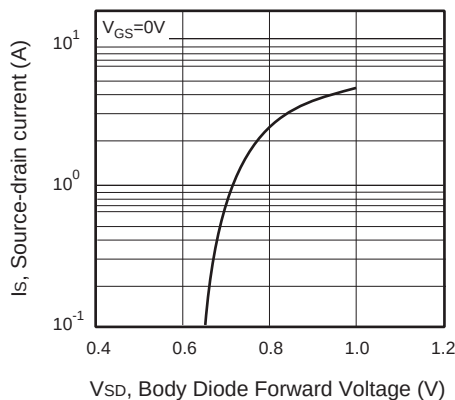


Figure 6. Body Diode Forward Voltage Variation with Source Current

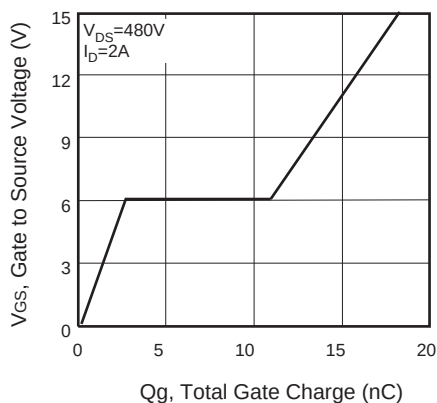


Figure 7. Gate Charge

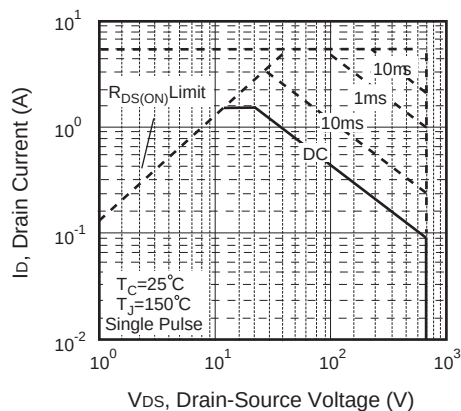


Figure 8. Maximum Safe Operating Area

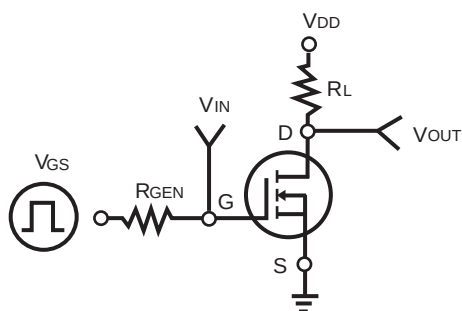


Figure 9. Switching Test Circuit

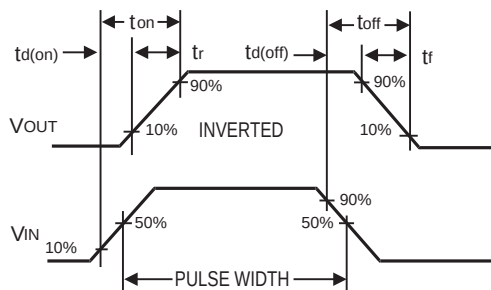


Figure 10. Switching Waveforms

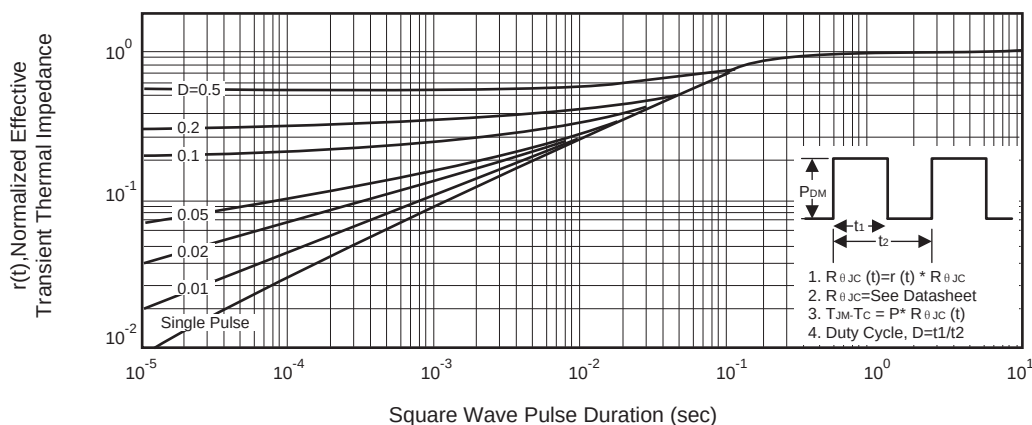


Figure 11. Normalized Thermal Transient Impedance Curve